

N-Channel 30-V (D-S) MOSFET

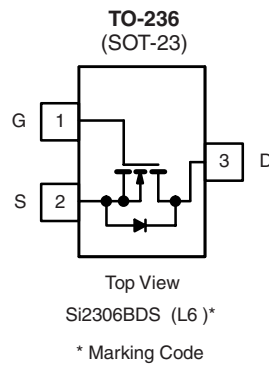
PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
30	0.047 at V _{GS} = 10 V	4.0	3.0
	0.065 at V _{GS} = 4.5 V	3.5	

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT



Ordering Information: Si2306BDS-T1-E3 (Lead (Pb)-free)
Si2306BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	30		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^{a, b}	I _D	T _A = 25 °C	4.0	3.16	A
		T _A = 70 °C	3.5	2.7	
Pulsed Drain Current	I _{DM}	20			
Continuous Source Current (Diode Conduction) ^{a, b}	I _S	1.04	0.62	W	
Maximum Power Dissipation ^{a, b}	P _D	T _A = 25 °C	1.25		0.75
		T _A = 70 °C	0.8		0.48
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	80	100	°C/W
		Steady State	130	166	
Maximum Junction-to-Foot (Drain)	R _{thJF}	60	75		

Notes:

- Surface Mounted on FR4 board, t ≤ 5 s.
- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 board.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted

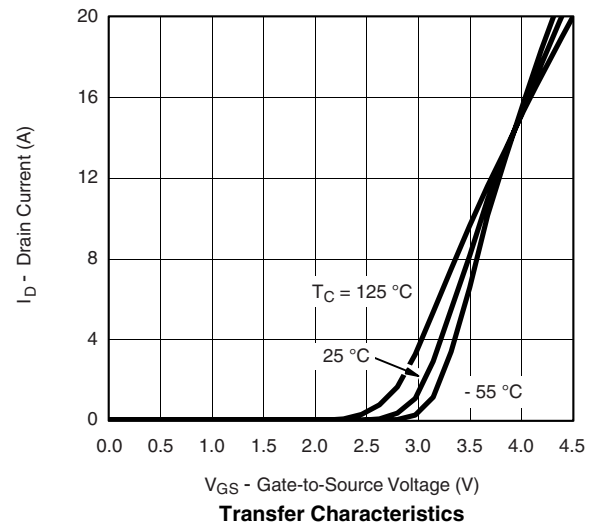
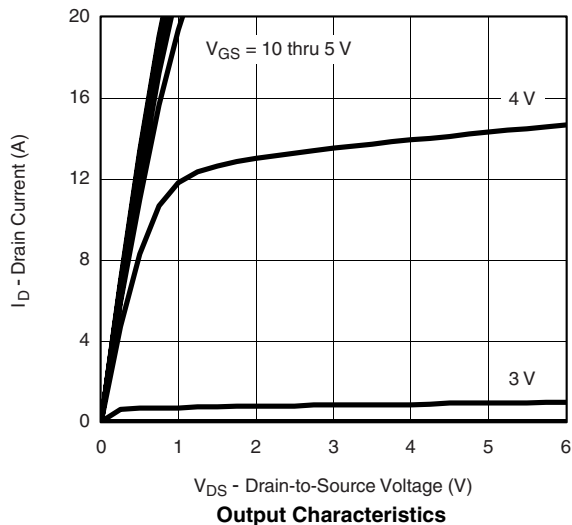
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			0.5	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 4.5\text{ V}, V_{GS} = 10\text{ V}$	6			A
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$		0.038	0.047	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 2.8\text{ A}$		0.052	0.065	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 4.5\text{ V}, I_D = 2.5\text{ A}$		7.0		S
Diode Forward Voltage	V_{SD}	$I_S = 1.25\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic						
Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 2.5\text{ A}$		3.0	4.5	nC
Total Gate Charge	Q_{gt}	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$		6	9	
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			0.6		
Gate Resistance	R_g	$f = 1.0\text{ MHz}$	2.5	5	7.5	Ω
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		305		pF
Output Capacitance	C_{oss}			65		
Reverse Transfer Capacitance	C_{rss}			29		
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		7	11	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			14	25	
Fall Time	t_f			6	10	
Reverse Recovery Time	t_{rr}	$I_F = 1.25\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		14	21	ns
Body Diode Reverse Recovery Charge	Q_{rr}			6	10	

Notes:

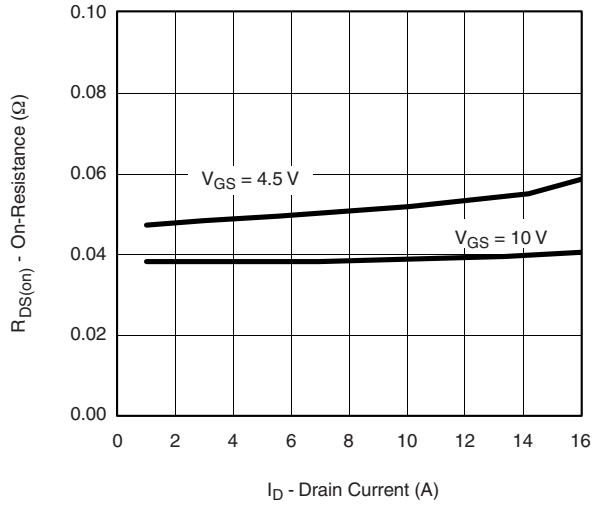
a. Pulse test: Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

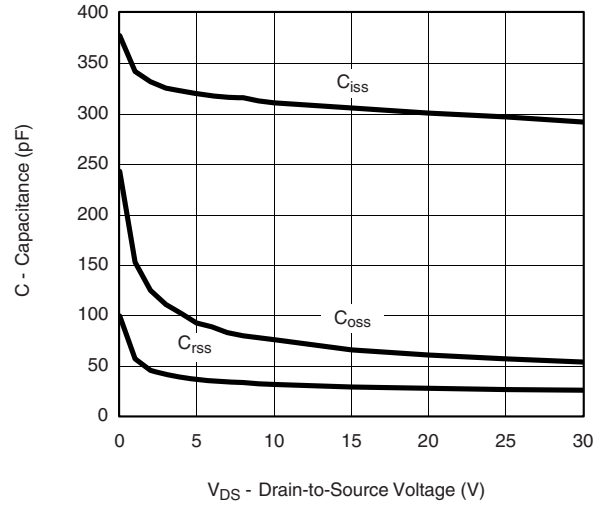
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



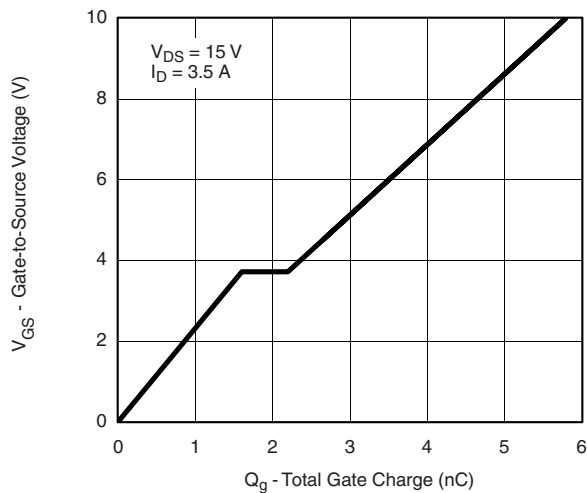
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



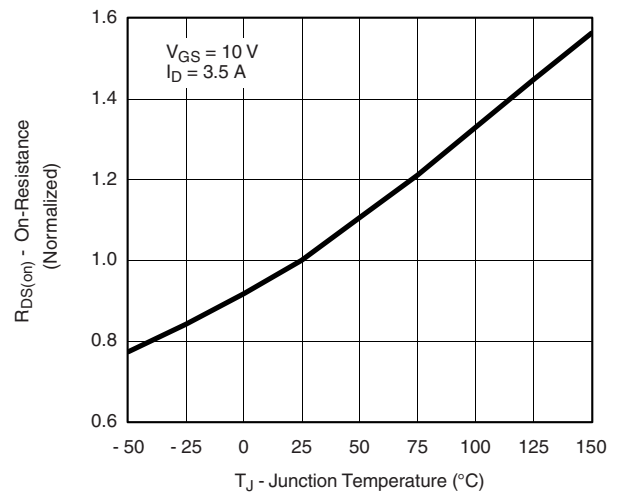
On-Resistance vs. Drain Current



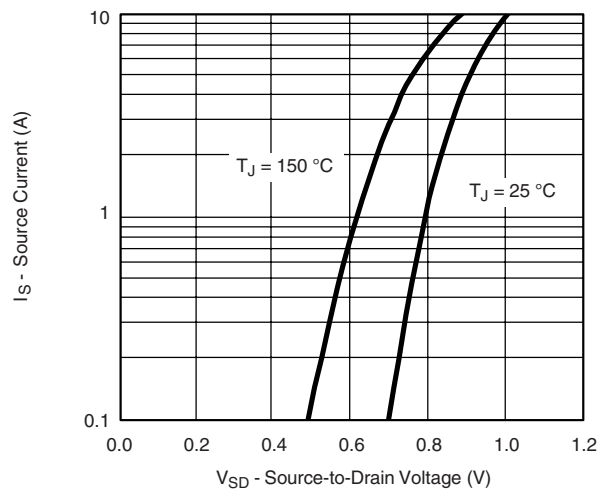
Capacitance



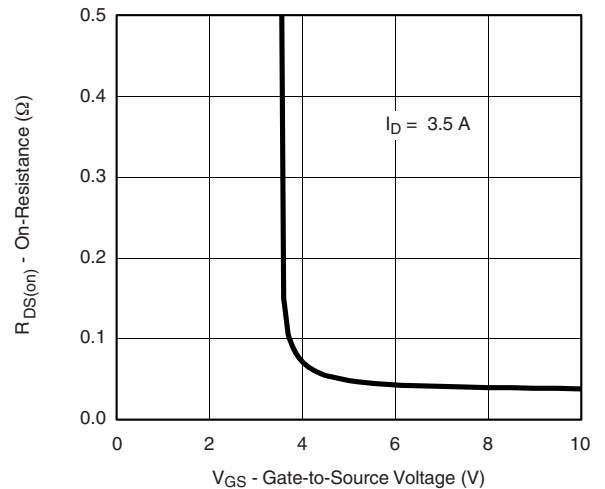
Gate Charge



On-Resistance vs. Junction Temperature

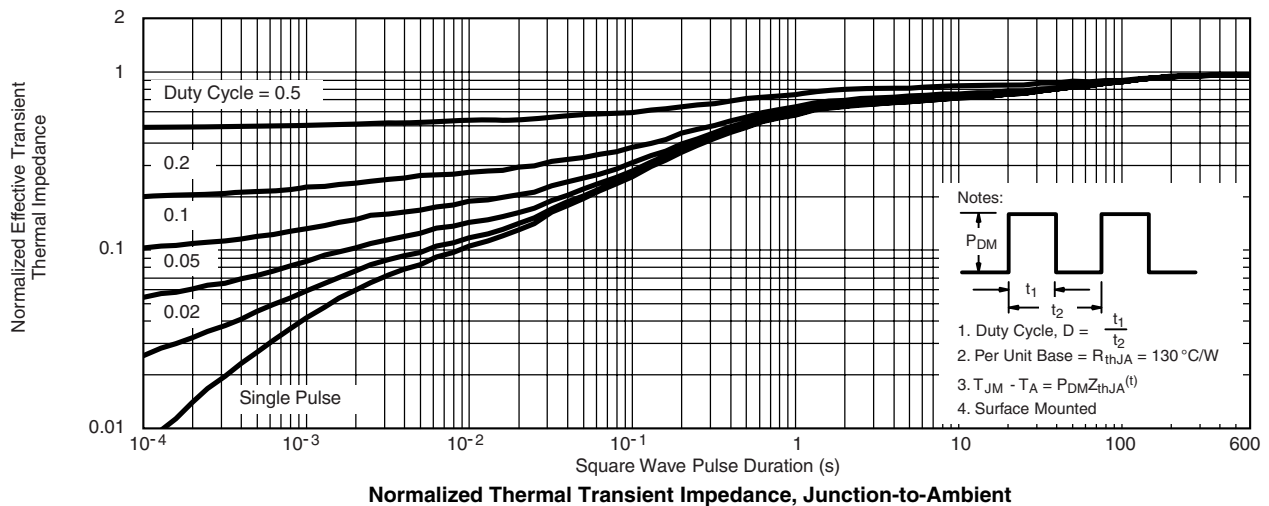
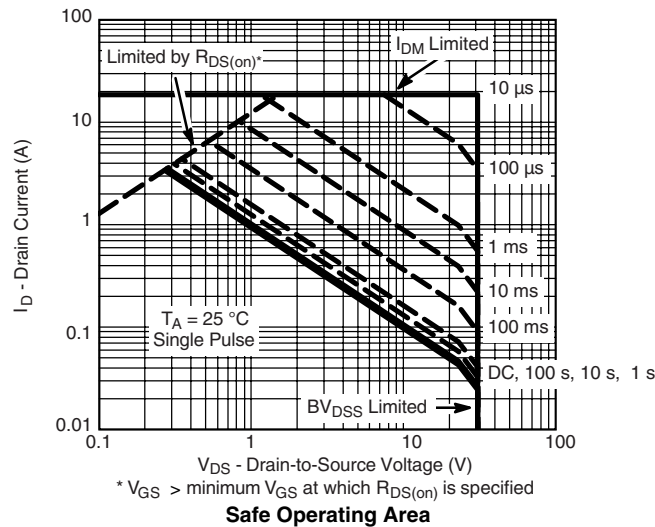
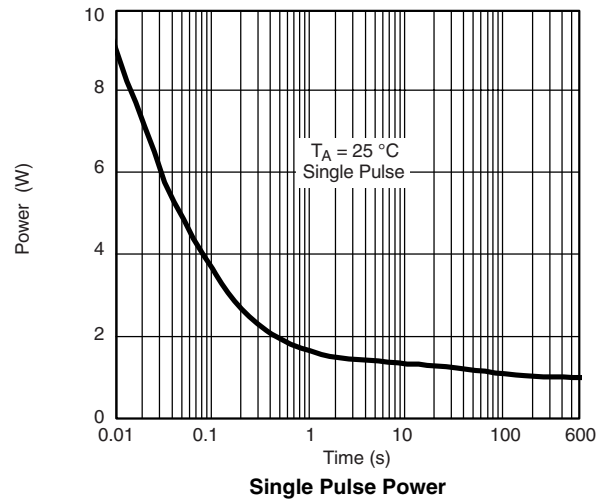
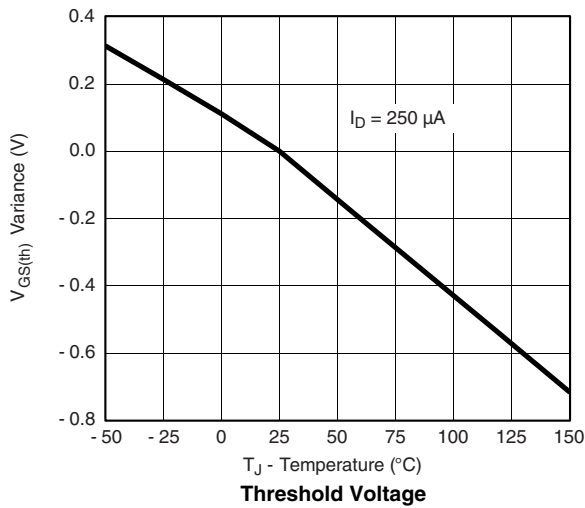


Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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